

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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In re Patent Application of:  
Euijoon Yoon et al.

Application No.: 10/563,854

Confirmation No.: 3828

Filed: June 9, 2006

Art Unit: 2823

For: GROWTH METHOD OF NITRIDE  
SEMICONDUCTOR EPITAXIAL LAYERS

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Examiner: Maldonado, Julio J.

DO NOT ENTER: /J.M./

**AMENDMENT AFTER FINAL ACTION (37 C.F.R. SECTION 1.116)**

February 8, 2010

MS AF  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

**INTRODUCTORY COMMENTS**

In response to the Final Office Action dated December 8, 2009, and with the Examiner's approval, please amend the above-identified U.S. patent application as follows:

**Amendments to the Claims** are reflected in the listing of claims which begins on page 2 of this paper.

**Remarks/Arguments** begin on page 8 of this paper.